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Yasufumi Fujiwara is a professor at the Department of Materials Science and Engineering at Osaka University in Japan, where he has been since 2003. His scientific interests include atomic-level controlled growth of III-V semiconductors (by means of organometallic vapour phase epitaxy), material science of electronic materials, and rare-earth-doped photonic devices.

Prof. Fujiwara earned his PhD degree in electrical engineering from Osaka University in 1986. He was a research associate (1985-1991) and an assistant professor (1991-1993) of Osaka University, and an associate professor of Nagoya University (1993-2003). He was also a visiting associate professor of the University of Illinois at Urbana-Champaign in USA (1995-1996). Fujiwara's research has resulted in over 150 refereed publications and, 140 international conference invited and contributed presentations. He has been a session chair for a number of international conferences and meetings. He can be reached at Osaka University, 2-1 Yamadaoka, Suita, Osaka 565-0871, Japan; tel. (+81)-6-6879-7498, fax. (+81)-6-6879-7499, and e-mail [fujiwara@mat.eng.osaka-u.ac.jp](mailto:fujiwara@mat.eng.osaka-u.ac.jp).

Prof. Fujiwara's recent publications in the field of rare-earth doped materials include:

- 1) A. Koizumi, **Y. Fujiwara**, A. Urakami, K. Inoue, T. Yoshikane and Y. Takeda: "Room-temperature electroluminescence properties of Er,O-codoped GaAs injection-type light emitting diodes grown by organometallic vapor phase epitaxy", *Applied Physics Letters* **83**(22), 4521 (2003).
- 2) **Y. Fujiwara**, A. Koizumi, A. Urakami, T. Yoshikane, K. Inoue and Y. Takeda: "Room-temperature 1.5 $\mu$ m electroluminescence from GaInP/Er,O-codoped GaAs/GaInP double heterostructure injection-type light emitting diodes grown by organometallic vapor phase epitaxy", *Materials Science and Engineering B* **105**(1-3), 57 (2003).
- 3) M. Yoshida, K. Hiraka, H. Ohta, **Y. Fujiwara**, A. Koizumi and Y. Takeda: "Electron spin resonance study of GaAs:Er,O grown by organometallic vapor phase epitaxy", *Journal of Applied Physics* **96**, 4189 (2004).
- 4) K. Nakamura, S. Takemoto, Y. Terai, M. Suzuki, A. Koizumi, Y. Takeda, M. Tonouchi and **Y. Fujiwara**: "Direct observation of trapping of photoexcited carriers in Er,O-codoped GaAs", *Physica B* **376-377**, 556 (2006).
- 5) **Y. Fujiwara**, S. Takemoto, K. Nakamura, K. Shimada, M. Suzuki, K. Hidaka, Y. Terai and M. Tonouchi: "Ultrafast carrier-trapping in Er-doped and Er,O-codoped GaAs revealed by pump and probe technique", *Physica B* (2007). [accepted for publication]